ABSTRACT OF THE DISCLOSURE

It is intended to provide a field-effective-type semiconductor device that can let low ON-resistance and non-excessive short-circuit current go together by effectively using its channel width and prevents device from destruction. In a field-effective-type semiconductor device, a semiconductor region arranged between gate electrodes 106 has stripe-patterned structure consisting of an N^+ emitter region 104 and a P emitter region. The P emitter region is constituted by P channel region 103 of low concentration and P^+ emitter region 100 of high concentration. The N^+ emitter region 104, the P channel region 103, and the P^+ emitter region 100 are in contact with the emitter electrode 109. Thereby, a channel width X is limited to the extent that is enough for ON current under normal operation state. That is, low ON-resistance and not excessive short-circuit current can go together in the field-effective-type semiconductor device.